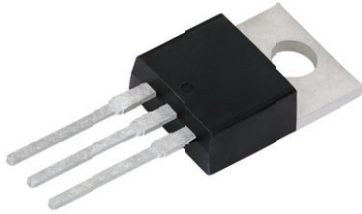
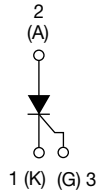




Thyristor High Voltage, Phase Control SCR, 10 A



3L TO-220AB



FEATURES

- Designed and qualified according to JEDEC®-JESD 47
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Typical usage is in input rectification crowbar (soft star) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-10TTS08... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

PRIMARY CHARACTERISTICS	
$I_{T(AV)}$	6.5 A
V_{DRM}/V_{RRM}	800 V
V_{TM}	1.15 V
I_{GT}	15 mA
T_J	-40 °C to 125 °C
Package	3L TO-220AB
Circuit configuration	Single SCR

OUTPUT CURRENT IN TYPICAL APPLICATIONS			
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
Capacitive input filter $T_A = 55\text{ °C}$, $T_J = 125\text{ °C}$, common heatsink of 1 °C/W	13.5	17	A

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	6.5	A
$I_{T(RMS)}$		10	
V_{RRM}/V_{DRM}		800	V
I_{TSM}		110	A
V_T	6.5 A, $T_J = 25\text{ °C}$	1.15	V
dV/dt		150	V/μs
dI/dt		100	A/μs
T_J	Range	-40 to +125	°C

VOLTAGE RATINGS			
PART NUMBER	V_{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V_{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM}/I_{DRM} AT 125 °C mA
VS-10TTS08-M3	800	800	1.0



ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum average on-state current	$I_{T(AV)}$	$T_C = 112\text{ }^\circ\text{C}$, 180° conduction half sine wave	6.5	A	
Maximum RMS on-state current	$I_{T(RMS)}$		10		
Maximum peak, one-cycle, non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied, $T_J = 125\text{ }^\circ\text{C}$	95		
		10 ms sine pulse, no voltage reapplied, $T_J = 125\text{ }^\circ\text{C}$	110		
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied, $T_J = 125\text{ }^\circ\text{C}$	45	A^2s	
		10 ms sine pulse, no voltage reapplied, $T_J = 125\text{ }^\circ\text{C}$	64		
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1\text{ ms to } 10\text{ ms}$, no voltage reapplied, $T_J = 125\text{ }^\circ\text{C}$	640	$A^2\sqrt{s}$	
Maximum on-state voltage drop	V_{TM}	6.5 A, $T_J = 25\text{ }^\circ\text{C}$	1.15	V	
On-state slope resistance	r_t	$T_J = 125\text{ }^\circ\text{C}$	17.3	$m\Omega$	
Threshold voltage	$V_{T(TO)}$		0.85	V	
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	$V_R = \text{Rated } V_{RRM}/V_{DRM}$	$T_J = 25\text{ }^\circ\text{C}$	0.05	mA
			$T_J = 125\text{ }^\circ\text{C}$	1.0	
Typical holding current	I_H	Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$, $T_J = 25\text{ }^\circ\text{C}$	30		
Maximum latching current	I_L	Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	50		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_{J\text{ max.}}$, linear to 80 %, $V_{DRM} = R_g - k = \text{Open}$	150	$V/\mu s$	
Maximum rate of rise of turned-on current	dI/dt		100	$A/\mu s$	

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}		8.0	W
Maximum average gate power	$P_{G(AV)}$		2.0	
Maximum peak positive gate current	$+I_{GM}$		1.5	A
Maximum peak negative gate voltage	$-V_{GM}$		10	V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, $T_J = -65\text{ }^\circ\text{C}$	20	mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	15	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	10	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = -65\text{ }^\circ\text{C}$	1.2	V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	1	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	0.7	
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125\text{ }^\circ\text{C}$, $V_{DRM} = \text{Rated value}$	0.2	
Maximum DC gate current not to trigger	I_{GD}		0.1	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t_{gt}	$T_J = 25\text{ }^\circ\text{C}$	0.8	μs
Typical reverse recovery time	t_{rr}	$T_J = 125\text{ }^\circ\text{C}$	3	
Typical turn-off time	t_q		100	



THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		-40 to +125	°C
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	1.5	°C/W
Maximum thermal resistance, junction to ambient	R_{thJA}		62	
Typical thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight			2	g
			0.07	oz.
Mounting torque	minimum		6 (5)	kgf · cm (lbf · in)
	maximum		12 (10)	
Marking device		Case style 3L TO-220AB	10TTS08	

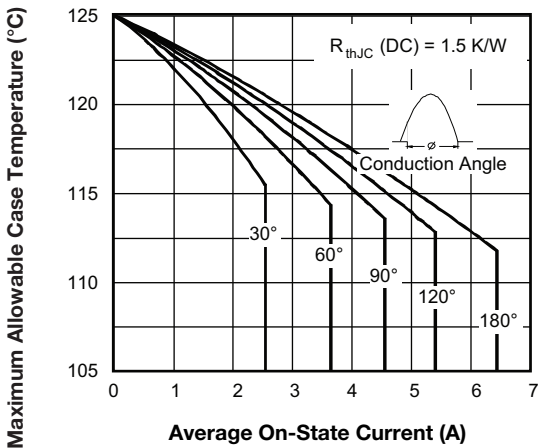


Fig. 1 - Current Rating Characteristics

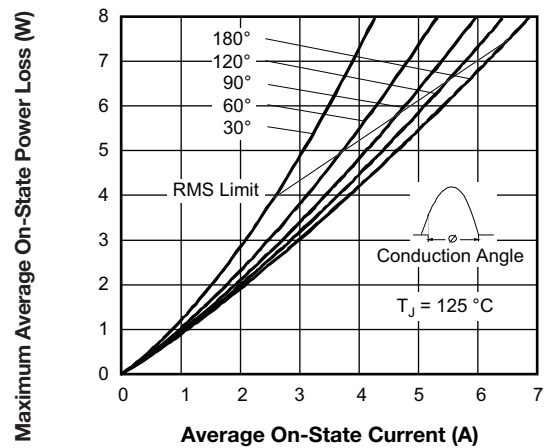


Fig. 3 - On-State Power Loss Characteristics

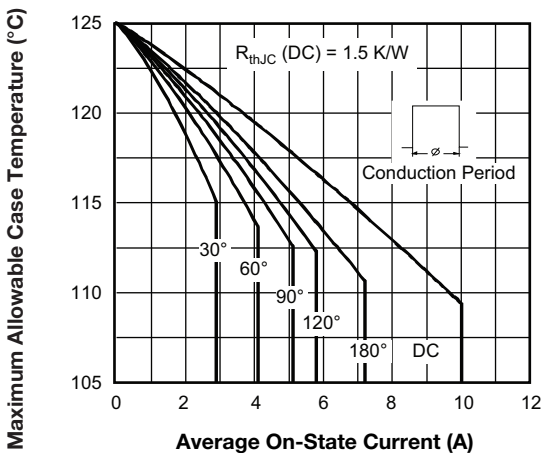


Fig. 2 - Current Rating Characteristic

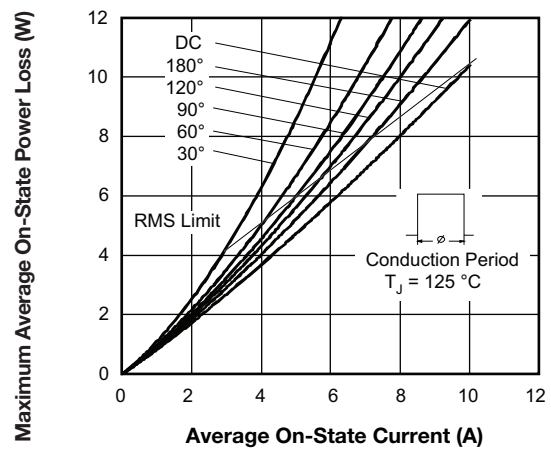


Fig. 4 - On-State Power Loss Characteristics

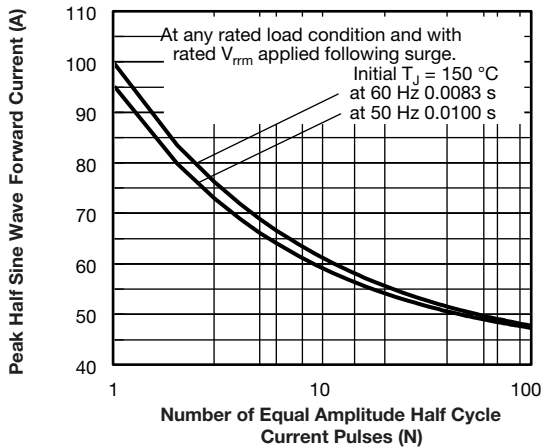


Fig. 5 - Maximum Non-Repetitive Surge Current

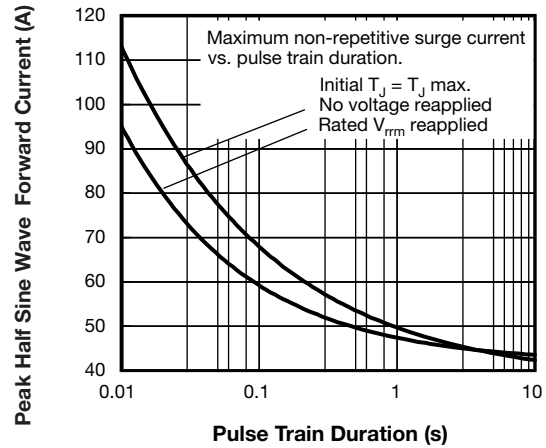


Fig. 6 - Maximum Non-Repetitive Surge Current

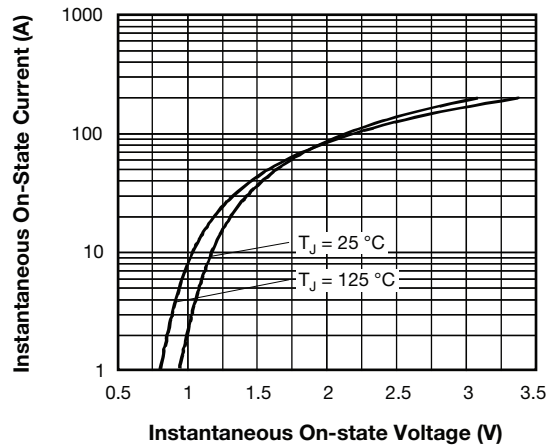


Fig. 7 - On-State Voltage Drop Characteristics

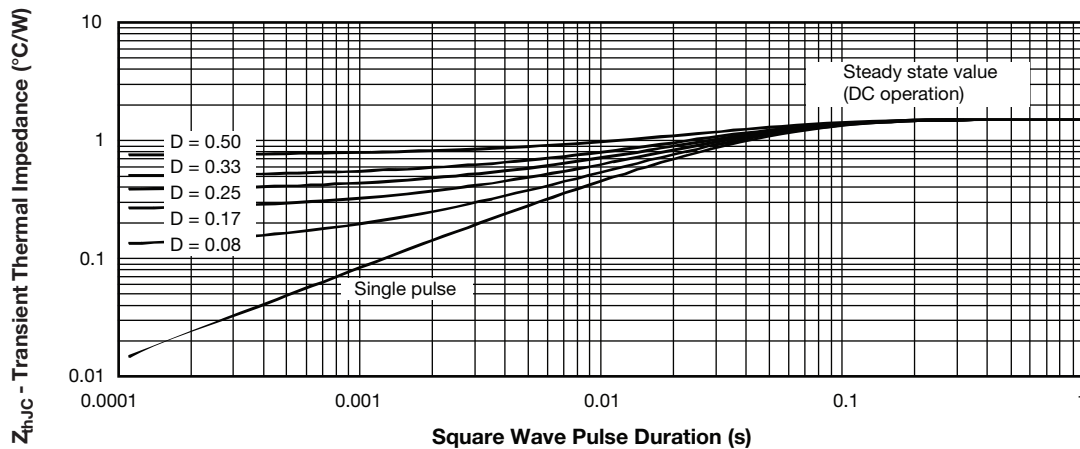
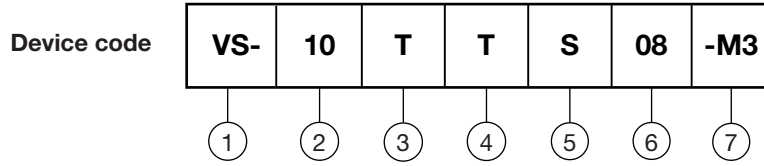


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics



ORDERING INFORMATION TABLE



- ① - Vishay Semiconductors product
- ② - Current rating
- ③ - Circuit configuration:
T = single thyristor
- ④ - Package:
T = TO-220AB
- ⑤ - Type of silicon:
S = converter grade
- ⑥ - Voltage code x 100 = V_{RRM}
- ⑦ - Environmental digit:
-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

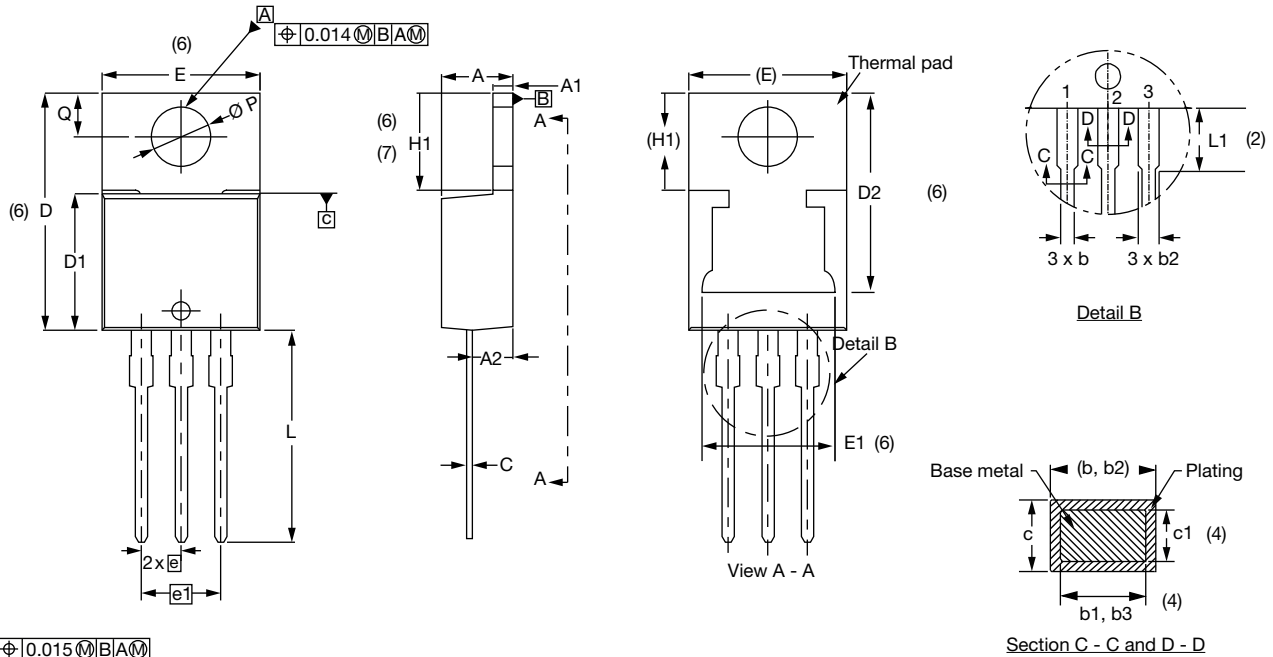
ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-10TTS08-M3	50	1000	Antistatic plastic tubes

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96154
Part marking information	www.vishay.com/doc?95028



3L TO-220AB

DIMENSIONS in millimeters and inches



Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
c	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
e	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
∅ P	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2 (minimum)



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